



Spec No.: DS70-2008-0032

Revision: A

Effective Date: 04/12/2016

**LITE-ON DCC** 

**RELEASE** 

BNS-OD-FC001/A4



### 1. DESCRIPTION

The 6N135/ 6N136-L consists of a high efficient AlGaAs Light Emitting Diode and a high speed optical detector. This design provides excellent AC and DC isolation between the input and output sides of the Optocoupler. Connection for the bias of the photodiode improves the speed that of a conventional phototransistor coupler by reducing the base-collector capacitances. The internal shield ensures high common mode transient immunity. A guaranteed common mode transient immunity is up to 1KV/µsec.

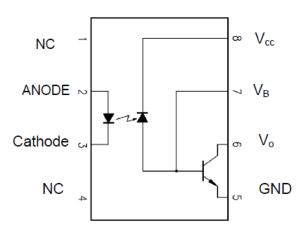
### 1.1 Features

- High speed 1MBd typical
- Available in Dual-in-line, Wide lead spacing, Surface mounting package.
- Storable output.
- UL, CSA approval

### 1.2 Applications

- Isolation in line receivers
- Digital isolation for A/D, D/A conversion
- Ground loop elimination
- Feedback Element in Switching Mode Power Supplier
- Pulse transformer replacement
- Power transistor isolation in motor drives
- Interface between Microprocessor system, computer and their peripheral

### 1.3 Functional Diagram



A 0.1µF bypass Capacitor must be connected between Pin8 and Pin5

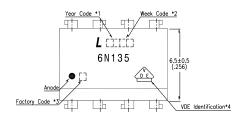
Truth Table (Positive Logic)

LED	OUT
ON	L
OFF	Н

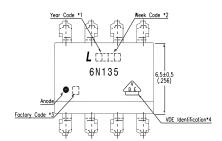


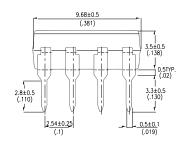
### 2. PACKAGE DIMENSIONS

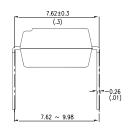
### 2.1 6N135-L

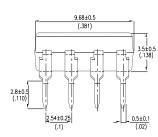


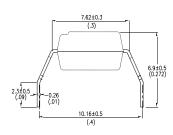
### 2.2 6N135M-L



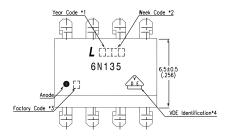


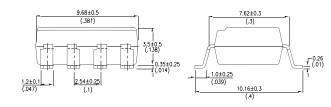






### 2.3 6N135S-L





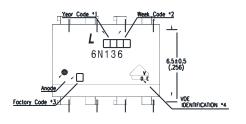
### Notes:

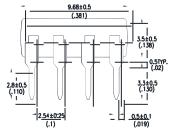
- 1. Year date code.
- 2. 2-digit work week.
- 3. Factory identification mark shall be marked (Y: Thailand , W: China-CZ)
- 4. For VDE option.

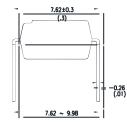
Dimensions in millimeters (inches).



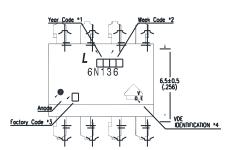
### 2.4 6N136-L

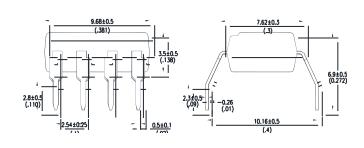




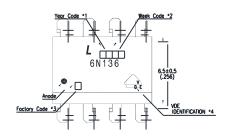


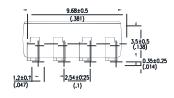
### 2.5 6N136M-L

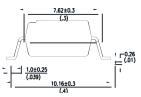




### 2.6 6N136S-L







### Notes:

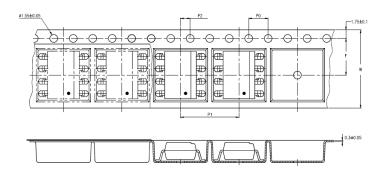
- 1. Year date code.
- 2. 2-digit work week.
- 3. Factory identification mark shall be marked (Y: Thailand , W: China-CZ)
- 4. For VDE option.

Dimensions in millimeters (inches).

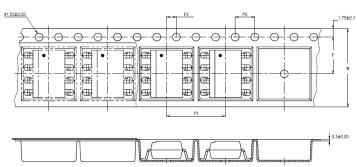


### 3. TAPING DIMENSIONS

### 3.1 6N135S-TA-L/ 6N136S-TA-L



### 3.2 6N135S-TA1-L/ 6N136S-TA1-L



Description	Symbol	Dimension in mm (inch)
Tape wide	W	16±0.3 (0.63)
Pitch of sprocket holes	P <sub>0</sub>	4±0.1 (0.15)
Distance of compartment	F	7.5±0.1 (0.295)
Distance of compartment	P <sub>2</sub>	2±0.1 (0.079)
Distance of compartment to compartment	P <sub>1</sub>	12±0.1 (0.472)

### 3.3 Quantities Per Reel

Package Type	TA / TA1
Quantities (pcs)	1000



### 4. RATING AND CHARACTERISTICS

### 4.1 Absolute Maximum Ratings at Ta=25°C \*1

	Parameter	Symbol	Rating	Unit	Note
	Average Forward Input Current	$I_F$	25	mA	2
loout	Reverse Input Voltage	$V_{R}$	5	V	
Input	Power Dissipation	Pı	45	mW	
	Junction temperature	$T_J$	125	°C	
	Output Collector Current	Io	8	mA	
Outout	Output Collector Voltage	Vo	20	V	
Output	Output Collector Power Dissipation	P <sub>o</sub>	100	mW	
	Junction temperature	$T_J$	125	°C	
	Isolation Voltage	$V_{ISO}$	5000	$V_{rms}$	
	Supply Voltage	V <sub>CC</sub>	15	V	
	Operating Temperature	$T_{opr}$	-40 ~ +85	°C	
	Storage Temperature	$T_{stg}$	-55 ~ +125	°C	
	Lead Solder Temperature *2	$T_{sol}$	260	°C	

- Ambient temperature = 25°C, unless otherwise specified. Stresses exceeding the absolute maximum ratings
  can cause permanent damage to the device. Exposure to absolute maximum ratings for long periods of time
  can adversely affect reliability.
- 2. 260°C for 10 seconds. Refer to Lead Free Reflow Profile.



### 4.2 ELECTRICAL OPTICAL CHARACTERISTICS at T<sub>A</sub> = 25°C

Parameters	Test Condition	Symbol	Device	Min	Тур	Max	Units
Input	•			•			
Input Forward Voltage	I <sub>F</sub> =16mA, T <sub>A</sub> =25°C	V <sub>F</sub>	6N135		1.4	1.7	V
Input Reverse Voltage	I <sub>R</sub> = 10μA T <sub>A</sub> =25℃	BV <sub>R</sub>	6N136	5	-	-	V
Detector							
	I <sub>F</sub> =16mA; Vo=0.4V;	077	6N135	7	18	50	- %
Current transfer ratio	V <sub>CC</sub> =4.5V; T <sub>A</sub> =25°C	CTR	6N136	19	24	50	
	I <sub>F</sub> =16mA;Vcc=4.5V;				0.40	0.4	
Logic low output voltage	I₀=1.1mA; T <sub>A</sub> =25°C	6N135	oN135 -	0.18	0.4	V	
Logic low output voltage	I <sub>F</sub> =16mA;Vcc=4.5V;	V OL	6N136	_	0.25	0.4	V
	I₀=3mA; T <sub>A</sub> =25°C				0.20	<b>U.</b>	
Logic high output current	$I_F$ =0mA, Vo=Vcc=5.5V; $T_A$ =25 $^{\circ}$ C		6N135	-	-	0.5	μ <b>Α</b>
Logic nigh output current	I <sub>F</sub> =0mA, Vo=Vcc=15V; T <sub>A</sub> =25°C	I <sub>OH</sub>	6N136	-	-	1	μΑ
Logic low supply current	I <sub>F</sub> =16mA, V₀=open (Vcc=15V)	6N135			400		<b>μ A</b>
Logic low supply culletti	iF=10iiiA, v₀=0peii (vcc=15v)	IccL	I <sub>ccL</sub> 6N136	-	400	-	μ 🖪
Logic high supply current	$I_F$ =0mA, $V_o$ =open ; $T_A$ =25 $^{\circ}$ C	1	6N135 I <sub>ссН</sub> 6N136		_	1	<b>μ A</b>
Logic High Supply Culterit	(Vcc=15V)	I CCH			_	'	$\mu N$

<sup>\*</sup> All Typical at T<sub>A</sub>=25°C



### 5. SWITCHING SPECIFICATION

Parameter	Test Condition	Symbol	Device	Min	Тур	Max	Units
Propagation Delay Time to	$T_A$ =25 $^{\circ}$ C $(R_L$ =4.1K $\Omega$ , $I_F$ =16mA)		6N135	-	0.09	1.5	
Low Output Level	$T_A=25^{\circ}\mathbb{C}$ (R <sub>L</sub> =1.9K $\Omega$ , I <sub>F</sub> =16mA)	t <sub>PHL</sub>	6N136	-	0.1	0.8	μ <b>s</b>
Propagation Delay Time to	$T_A=25^{\circ}$ C $(R_L=4.1K\Omega,I_F=16mA)$		6N135	-	0.8	1.5	
High Output Level	$T_A$ =25 $^{\circ}$ C ( $R_L$ =1.9 $K\Omega$ , $I_F$ =16 $mA$ )	t <sub>PLH</sub>	6N136	-	0.4	0.8	μ <b>s</b>
Logic High Common Mode	$I_F$ =0mA; $V_{CM}$ =10Vp-p; $R_L$ =4.1K $\Omega$ ; $T_A$ =25C	IOM I	6N135	4	40		KV/µs
Transient Immunity	$I_F$ =0mA; $V_{CM}$ =10Vp-p; $R_L$ =1.9K $\Omega$ ; $T_A$ =25C	CM <sub>H</sub>	6N136	1	10	-	KV/µs
Logic Low Common Mode	$I_F$ =0mA; $V_{CM}$ =10Vp-p; $R_L$ =4.1K $\Omega$ ; $T_A$ =25C	IOM	6N135	4	40		KV/µs
Transient Immunity	$I_F$ =0mA; $V_{CM}$ =10Vp-p; $R_L$ =1.9K $\Omega$ ; $T_A$ =25C	CM <sub>L</sub>	6N136	1	10	-	KV/µs

<sup>\*</sup>  $T_A \!\!=\!\! 0 \!\!\sim\!\! 70^{\circ}\!\!\! \text{C}$  , Vcc=5V, unless otherwise specified.

<sup>\*</sup> All Typical at  $T_A$ =25°C



### 6. ISOLATION CHARACTERISTIC

Parameter	Symbol	Min.	Тур.	Max.	Unit	Test Condition
Input-Output Insulation Leakage Current	I <sub>I-O</sub>	_	_	1.0	μΑ	45% RH, t = 5s, V <sub>I-O</sub> = 3kV DC, T <sub>A</sub> =25°C
Withstand Insulation Test Voltage	$V_{\rm ISO}$	5000	_	_	$V_{RMS}$	RH $\leq$ 50%, t = 1min, T <sub>A</sub> = 25°C
Input-Output Resistance	R <sub>I-O</sub>	—	10 <sup>12</sup>	_	Ω	V <sub>I-O</sub> = 500V DC

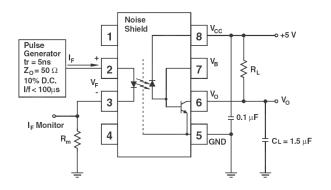
<sup>\*</sup>All Typical at T<sub>A</sub> =25°C

#### **Notes**

- 1. A 0.1  $\mu F$  or bigger bypass capacitor for  $V_{\text{CC}}$  is needed as shown in Fig.1
- 2. Current Transfer Ratio is defined as the ratio of output collector current Io, to the forward LED input current IF, times 100.
- 3. The 1.9K $\!\Omega$  load represents 1TTL unit load of 1.6mA and the 5.6K $\!\Omega$  pull-up resistor.
- 4. The 4.1K  $\!\Omega$  load represents 1LSTTL unit load of 0.36mA and the 6.1K  $\!\Omega$  pull-up resistor.



### 7. SWITCHING TIME TEST CIRCUIT



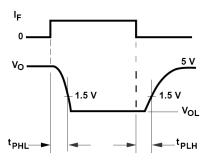


Figure 1: Test Circuit for t<sub>PHL</sub> and t<sub>PLH</sub>

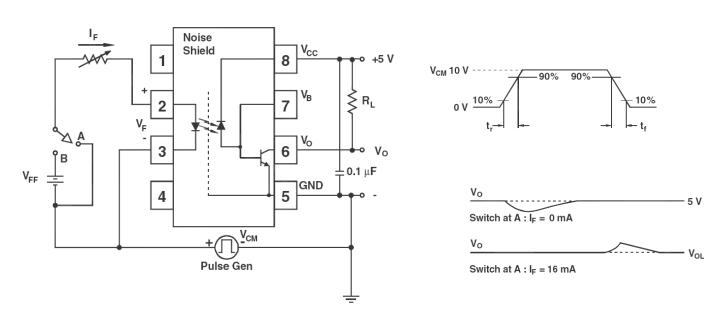


Figure 2: Single Channel Test Circuit for Common Mode Transient Immunity



### 8. CHARACTERISTIC CURVES

Figure 3: DC and pulsed transfer characteristics

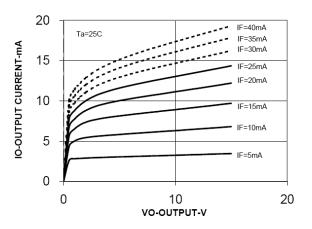


Figure 4: Input current vs. forward voltage

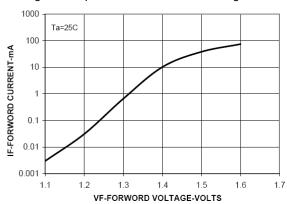


Figure 5: Logic high output current vs. temperature

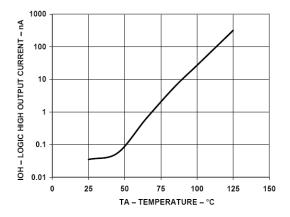


Figure 6: Current transfer ratio vs. input current

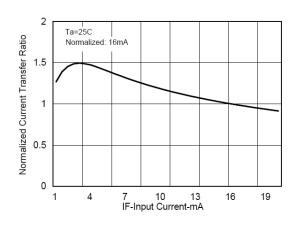


Figure 7: Current transfer ratio vs. temperature

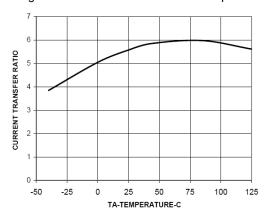


Figure 8: Small-signal current transfer ratio vs.

quiescent current

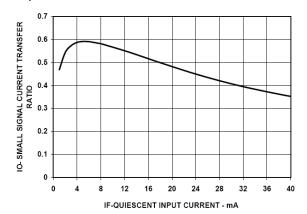




Figure 9: Propagation delay time vs. temperature

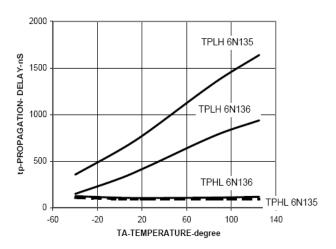
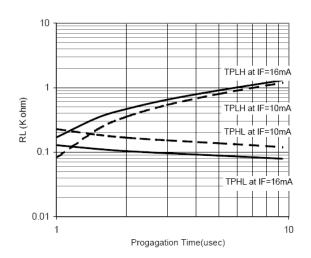


Figure 10: Propagation delay time vs. load resistance



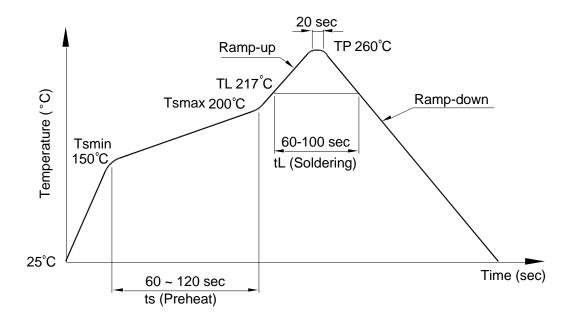


### 9. TEMPERATURE PROFILE OF SOLDERING

### 9.1 IR Reflow soldering (JEDEC-STD-020C compliant)

One time soldering reflow is recommended within the condition of temperature and time profile shown below. Do not solder more than three times.

Profile item	Conditions			
Preheat				
- Temperature Min (T <sub>Smin</sub> )	150°C			
- Temperature Max (T <sub>Smax</sub> )	200°C			
- Time (min to max) (ts)	90±30 sec			
Soldering zone				
- Temperature (T <sub>L</sub> )	217°C			
- Time (t <sub>L</sub> )	60 ~ 100 sec			
Peak Temperature (T <sub>P</sub> )	260°C			
Ramp-up rate	3°C / sec max.			
Ramp-down rate	3~6°C / sec			





### 9.2 Wave soldering (JEDEC22A111 compliant)

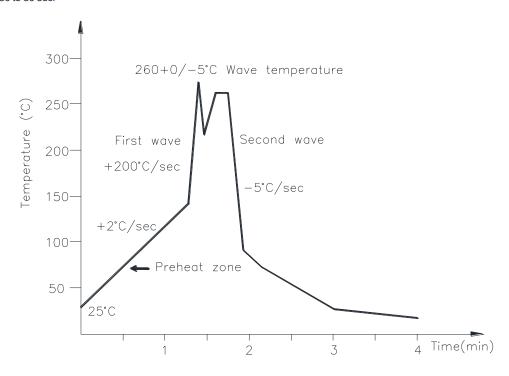
One time soldering is recommended within the condition of temperature.

Temperature: 260+0/-5°C

Time: 10 sec.

Preheat temperature:25 to 140°C

Preheat time: 30 to 80 sec.



### 9.3 Hand soldering by soldering iron

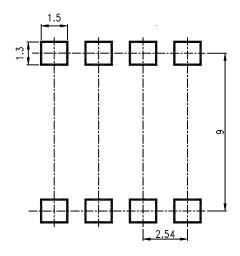
Allow single lead soldering in every single process. One time soldering is recommended.

Temperature: 380+0/-5°C

Time: 3 sec max.



### 10. RECOMMENDED FOOT PRINT PATTERNS (MOUNT PAD)

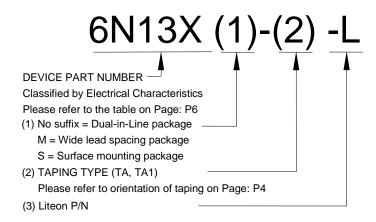


### Note:

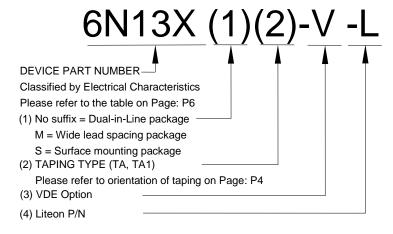
Dimensions in millimeters.



### 11. NAMING RULE



Example: 6N135S-TA1-L, 6N136S-TA1-L



Example: 6N135STA1-V-L, 6N136STA1-V-L

### 12. NOTES

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- The products shown in this publication are designed for the general use in electronic applications such as office automation equipment, communications devices, audio/visual equipment, electrical application and instrumentation.
- For equipment/devices where high reliability or safety is required, such as space applications, nuclear power control equipment, medical equipment, etc, please contact our sales representatives.
- When requiring a device for any "specific" application, please contact our sales in advice.
- If there are any questions about the contents of this publication, please contact us at your convenience.
- The contents described herein are subject to change without prior notice.
- Immerge unit's body in solder paste is not recommended.